

HAT2179R

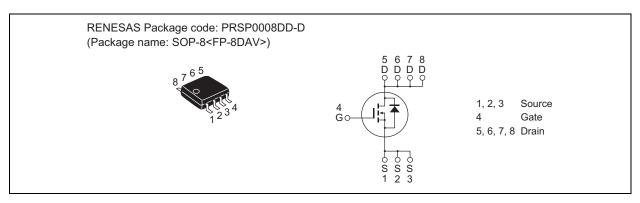
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1570-0100 Rev.1.00 Jul 06, 2007

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit	
Drain to source voltage	V_{DSS}	600	V	
Gate to source voltage	V_{GSS}	±30	V	
Drain current	I _D	0.7	Α	
Drain peak current	I _{D (pulse)} Note1	2.0	Α	
Body-drain diode reverse drain current	I _{DR}	0.7	Α	
Body-drain diode reverse drain peak current	I _{DR (pulse)} Note1	2.0	Α	
Channel dissipation	Pch Note2	2.5	W	
Channel temperature	Tch	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW \leq 10 s

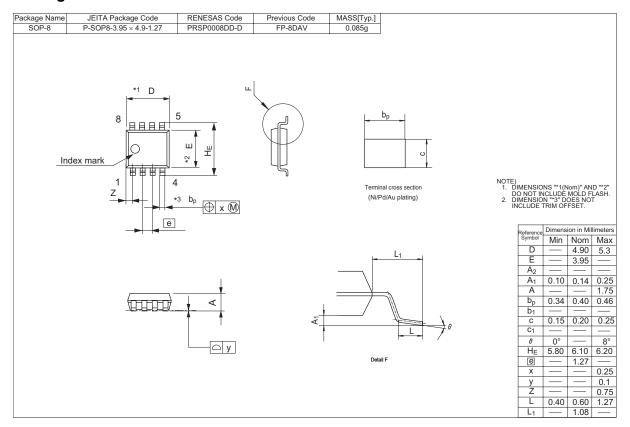
Electrical Characteristics

 $(Ta = 25^{\circ}C)$

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	600	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I _{GSS}			±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	3.0		5.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward transfer admittance	yfs	8.0	1.2	_	S	$I_D = 0.4 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note3}}$
Static drain to source on state	R _{DS(on)}	_	3.5	4.5	Ω	$I_D = 0.4 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note3}}$
resistance						
Input capacitance	Ciss		280	_	pF	V _{DS} = 25 V
Output capacitance	Coss		31	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss		3.8	_	pF	f = 1 MHz
Turn-on delay time	t _{d(on)}	_	24	_	ns	I _D = 0.4 A
Rise time	t _r	_	15	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	50	_	ns	$R_L = 750 \Omega$
Fall time	t _f	_	58	_	ns	$Rg = 10 \Omega$
Total gate charge	Qg	_	10	_	nC	V _{DD} = 480 V
Gate to source charge	Qgs	_	1.6	_	nC	V _{GS} = 10 V
Gate to drain charge	Qgd	_	5.4	_	nC	$I_D = 0.7 A$
Body-drain diode forward voltage	V_{DF}	_	0.8	1.2	V	$I_F = 0.7 \text{ A}, V_{GS} = 0^{\text{Note3}}$
Body-drain diode reverse	t _{rr}	_	200	_	ns	$I_F = 0.7 \text{ A}, V_{GS} = 0$
recovery time						$di_F/dt = 100 A/\mu s$

Notes: 3. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2179R-EL-E	2500 pcs	Taping

Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas Technology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

 Notes:

 1. This document is provided for reference purposes only so that Penesas customers may select the appropriate Renesas products for their use. Renesas neither makes in the selection of the provided for reference purposes only so that Penesas customers may select the appropriate Renesas products for their use. Renesas neither makes are all the comment of any intellectual property or other rights arising out of the use of any intellectual property rights or any other rights of Renesas or any third party with respect to the information in this document nor grants any license to any intellectual property or other rights arising out of the use of any information in this document, including, but not limited to, product data, diagrams, charts, programs, algorithms, and application circuit examples.

 3. You should not use the products or the technology described in this document for the purpose of military applications such as the development of waspons of mass and included in this document such as product data, diagrams, and regulations, and procedures required by such law and regulations and procedures required by such law and regulations. However, is subject to change without any prior notice. Before purchasing or using any Reneasa products itself in this document, but all information in included in this document, but any continuous and procedure and such as the disclosed by Reneasa such as hat disclosed through our website, (http://www.renesas.com/

 4. All information included in this document. Such as a su



RENESAS SALES OFFICES

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology Singapore Pte. Ltd. 1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510